

Power-Gate Ring

2.5 - 25W

Frequency >3GHz

Process
32nm high-k metal-gate (HKMG) SOI Process
Core
9.69mm2
35 M Transistors
Core + 1MB L2 + Power-Gate Ring
17.7mm2
110 M Transistors
Voltage
0.8 - 1.3V
Power

Architectural Improvements

Bigger instruction window For more integer/FP execution throughput (72-entry to 84-entry)

Hardware integer divide

Lower latency FP instructions

Enhanced data prefetching

Faster memory fills and cache state transitions

I/O-based C-states including full processor state save

Enhanced TLB residency for virtualization